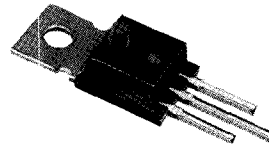


D



E

Silicon npn high voltage transistors

Photographs actual size

Type	V _{CEO} max. V	V _{CBO} max. V	V _{EBO} max. V	I _C max. A	P _{tot} max. @		V _{CEO(sus)} min. V	T _j max. °C	V _{CE(sat)} max. V	@ I _C & I _B		h _{FE} @ I _C & V _{CE}		f _T typ. MHz	Out- line		
					T _{case} = 75°C	W				A	A	min.	max.			A	V
DT1003 DT1013	200	200	5	0.3	4(1)			125	0.6	0.2	0.04	12 30	36 90	0.2 0.2	6 6	1 1	A
DT4305 DT4306	300 375	400 500	5	5	30(2)		265 325	125	1.5	3	0.6	10	50	3	5	3	G
*DT4423 *DT4424 *DT4425	400 500 500	400	5 6 6	3.5	100		325 350 400	150	0.8	1	0.1	30	90	1	5	4 2.5(3) 2.5(3)	G
*DT4430 *DT4431	400	400	5	5.0	125(4)		300 325	150	0.9 0.7	2.5 2.5	0.5 0.5	15 15	45 35	2.5 2.5	5 5	4.0	G
DT6105 DT6106	300 375	400 500	5	10	50		265 325	125	3	5	1	10	50	3	5	5	D
*2N2580 *2N2581 *2N2582 *2N2583	400 400 500 500	400	5	10	150(1)		325	150	0.7 1.0 0.7 1.0	5 10 5 10	1 2 1 2	10 25 10 25	40 65 40 65	5 10 5 10	5 5 5 5		D
*2N3079 *2N3080	200 300	200 300	5	5	150(1)		200 300	150	0.7	5	1	10	50	5	5		D
*2N3902	400		5	3.5	100		325	150	0.8	1	0.1	30	90	1	5	4.0	G
*2N5157	500	700	6	3.5	100		400	150	0.8	1	0.1	30	90	1	5		G
*2N5241	400	400	5	5	125(4)		325	150	0.7	2.5	0.5	15	35	2.5	5		G

*New devices.

(1) T_{case} = 45°C. (2) T_{case} = 65°C. (3) f_T min. (4) T_{case} = 62.5°C.

Darlington power transistors

Type	V _{CEO(sus)} V	V _{CBO} max. V	V _{EBO} max. V	I _C max. A	P _{tot} max. W	T _j max. °C	I _{CBO} max. µA	@ V _{CB} & T _{amb}		h _{FE} @ I _C		V _{CE(sat)} max. V	I _C A	Out- line	
								V	°C	min.	max.				A
*DT3410 *DT3411 *DT3420 *DT3421	40 80 40 80	40 80	5	5	7(5)	150	10	40 80 40 80	25	1000 1000 1750 1750	— — — —	2 2 2 2	1.7	3	E
*DT3410A *DT3411A *DT3420A *DT3421A	40 80 40 80	40 80	5	5	17.5(6)	150	10	40 80 40 80	25	1000 1000 1750 1750	— — — —	2 2 2 2	1.7	3	F

*New devices.

(5) T_{amb} = 25°C. (6) T_{case} = 25°C.